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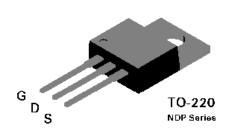
NDP6030PL / NDB6030PL P-Channel Logic Level Enhancement Mode Field Effect Transistor

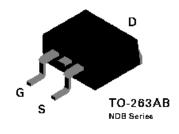
General Description

These P-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage applications such as DC/DC converters and high efficiency switching circuits where fast switching, low in-line power loss, and resistance to transients are needed.

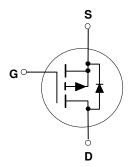
Features

- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High density cell design for extremely low R_{DS(ON)}.
- 175°C maximum junction temperature rating.





NDP6030PL



NDB6030PL

Absolute Maximum Ratings T_c = 25°C unless otherwise noted

V _{DSS}	Drain-Source Voltage	-30	V
V _{GSS}	Gate-Source Voltage - Continuous	±16	V
I _D	Drain Current - Continuous	-30	Α
	- Pulsed	-90	
P _D	Total Power Dissipation @ T _C = 25°C	75	W
	Derate above 25°C	0.5	
T _J ,T _{STG}	Operating and Storage Temperature Range	-65 to 175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275	°C
T _J ,T _{STG}	Operating and Storage Temperature Range	-65 to 175	°C

THERMAL CHARACTERISTICS

Parameter

Symbol

R _{euc}	Thermal Resistance, Junction-to-Case	2	°C/W
R _{eJA}	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Units

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
OFF CHAR	ACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		-30			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	I _D = -250 μA, Reference	I _D = -250 μA, Referenced to 25 °C		-36		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$				-250	μΑ
			T _J = 125°C			1	mA
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 16 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -16 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHARAC	CTERISTICS (Note)	·			•		•
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp.Coefficient	I _D = -250 μA, Reference	I _D = -250 μA, Referenced to 25 °C		2.2		mV/°C
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		-1	-1.4	-2	V
,			T _J = 125°C	-0.8	-1.08	-1.6	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_{D} = -15 \text{ A}$			0.037	0.042	Ω
			T _J = 125°C		0.053	0.075	
		$V_{GS} = -10 \text{ V}, I_{D} = -19 \text{ A}$			0.021	0.025	
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$		-20			Α
g _{FS}	Forward Transconductance	$V_{DS} = -4.5 \text{ V}, I_{D} = -19 \text{ A}$			20		S
DYNAMIC C	HARACTERISTICS	•		•	•	3	•
C _{iss}	Input Capacitance	$V_{DS} = -15 \text{ V}, \ V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$			1570		pF
C _{oss}	Output Capacitance				975		pF
C _{rss}	Reverse Transfer Capacitance				360		pF
	CHARACTERISTICS (Note)			ı		ı	
t _{D(on)}	Tum - On Delay Time	$V_{DD} = -15 \text{ V}, \ I_D = -5 \text{ A},$ $V_{GS} = -5 \text{ V}, \ R_{GEN} = 6 \Omega$			12.5	25	nS
t.	Turn - On Rise Time				60	120	nS
t _{D(off)}	Turn - Off Delay Time				50	100	nS
t _f	Turn - Off Fall Time				52	100	nS
Q _q	Total Gate Charge	V _{DS} = -12 V			26	36	nC
\overline{Q}_{gs}	Gate-Source Charge	$I_{D} = -30 \text{ A}, V_{GS} = -5 \text{ V}$			6.5		nC
Q_{gd}	Gate-Drain Charge				11.5		nC
	RCE DIODE CHARACTERISTICS					I	1
I _s	Maximum Continuos Drain-Source Diode Forward Current					-30	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward					-100	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -15 A (No	$V_{GS} = 0 \text{ V}, I_{S} = -15 \text{ A} \text{ (Note)}$		-0.92	-1.3	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{F} = -30 \text{ A}$			58		ns
Irr	Reverse Recovery Current	$dI_{F}/dt = 100 A/\mu s$			-1.5		Α

Pulse Test: Pulse Width $\leq 300 \ \mu s$, Duty Cycle $\leq 2.0\%$.

Typical Electrical Characteristics

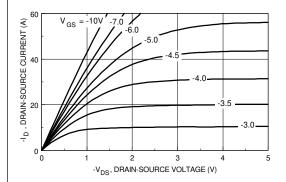


Figure 1. On-Region Characteristics.

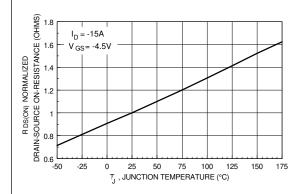


Figure 3. On-Resistance Variation with Temperature.

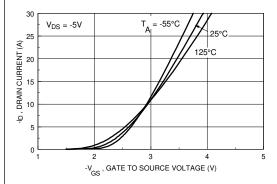


Figure 5. Transfer Characteristics.

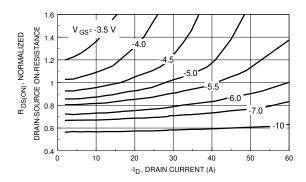


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

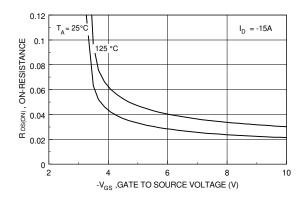


Figure 4. On Resistance Variation with Gate-To- Source Voltage.

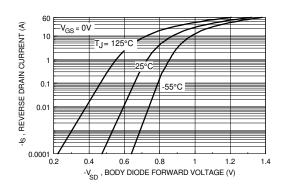


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics (continued)

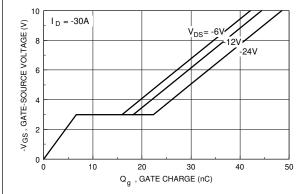


Figure 7. Gate Charge Characteristics.

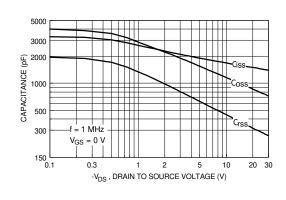


Figure 8. Capacitance Characteristics.

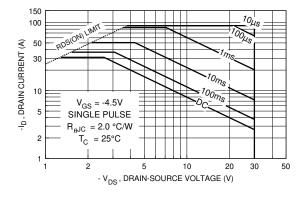


Figure 9. Maximum Safe Operating Area.

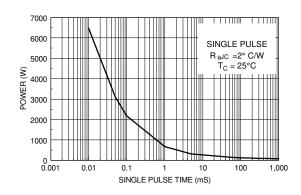


Figure 10. Single Pulse Maximum Power Dissipation.

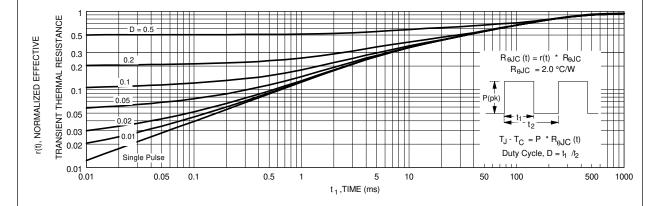


Figure 11. Transient Thermal Response Curve.

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